

DS1109SG

RECTIFIER DIODE

APPLICATIONS

- Rectification.
- Freewheel Diode.
- DC Motor Control.
- Power Supplies.
- Welding.
- Battery Chargers.

KEY PARAMETERS

V_{RRM}	5000V
$I_{F(AV)}$	710A
I_{FSM}	11500A

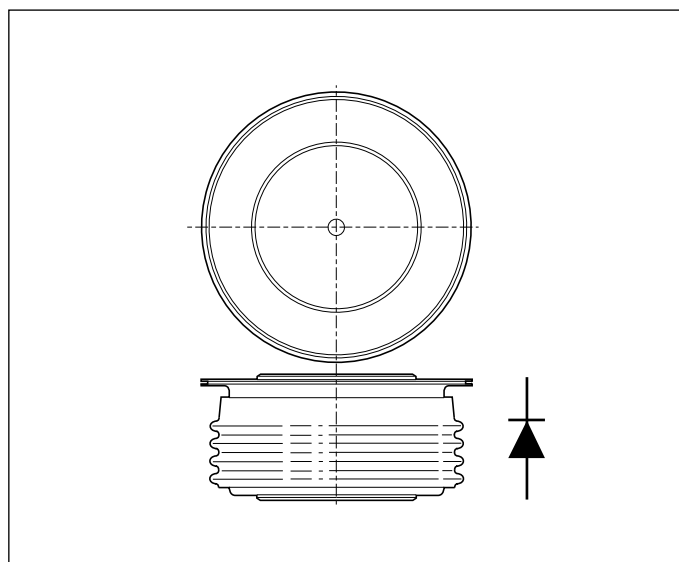
FEATURES

- Double Side Cooling.
- High Surge Capability.

VOLTAGE RATINGS

Type Number	Repetitive Peak Reverse Voltage V_{RRM} V	Conditions
DS1109SG50 DS1109SG49 DS1109SG48 DS1109SG47 DS1109SG46 DS1109SG45	5000 4900 4800 4700 4600 4500	$V_{RSM} = V_{RRM} + 100V$

Lower voltage grades available.



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CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, $T_{case} = 100^{\circ}C$	710	A
$I_{F(RMS)}$	RMS value	$T_{case} = 100^{\circ}C$	1115	A
I_F	Continuous (direct) forward current	$T_{case} = 100^{\circ}C$	1000	A
Single Side Cooled (Anode side)				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, $T_{case} = 100^{\circ}C$	450	A
$I_{F(RMS)}$	RMS value	$T_{case} = 100^{\circ}C$	706	A
I_F	Continuous (direct) forward current	$T_{case} = 100^{\circ}C$	570	A

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; $T_{case} = 150^{\circ}C$ $V_R = 50\% V_{RRM} - 1/4$ sine	9.2	kA
I^2t	I^2t for fusing		422×10^3	A ² s
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; $T_{case} = 150^{\circ}C$ $V_R = 0$	11.5	kA
I^2t	I^2t for fusing		660×10^3	A ² s

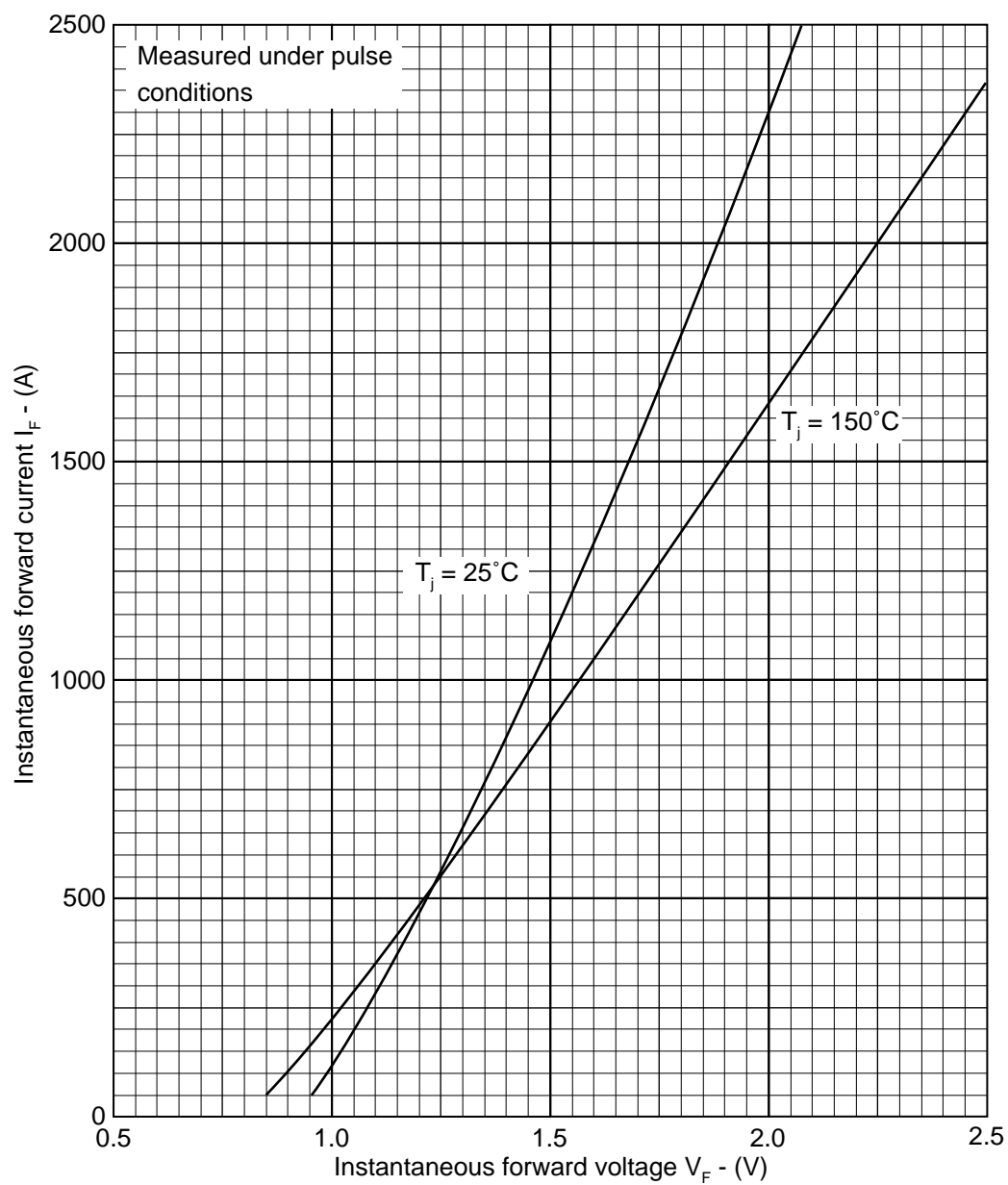
THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.032	$^{\circ}C/W$
		Single side cooled	Anode dc	-	0.064	$^{\circ}C/W$
			Cathode dc	-	0.064	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 12.0kN with mounting compound	Double side	-	0.008	$^{\circ}C/W$
			Single side	-	0.016	$^{\circ}C/W$
T_{vj}	Virtual junction temperature	Forward (conducting)		-	160	$^{\circ}C$
		Reverse (blocking)		-	150	$^{\circ}C$
T_{stg}	Storage temperature range			-55	175	$^{\circ}C$
-	Clamping force			11.5	13.5	kN

CHARACTERISTICS

Symbol	Parameter	Conditions	Min.	Max.	Units
V_{FM}	Forward voltage	At 1800A peak, $T_{case} = 25^{\circ}C$	-	1.8	V
I_{RRM}	Peak reverse current	At V_{RRM} , $T_{case} = 150^{\circ}C$	-	50	mA
Q_S	Total stored charge	$I_F = 1000A$, $di_{RR}/dt = 3A/\mu s$ $T_{case} = 150^{\circ}C$, $V_R = 100V$	-	2600	μC
I_{RR}	Peak recovery current		-	80	A
V_{TO}	Threshold voltage	At $T_{vj} = 150^{\circ}C$	-	0.88	V
r_T	Slope resistance	At $T_{vj} = 150^{\circ}C$	-	0.687	m Ω

CURVES

**FIG. 1 MAXIMUM (LIMIT) FORWARD CHARACTERISTICS**

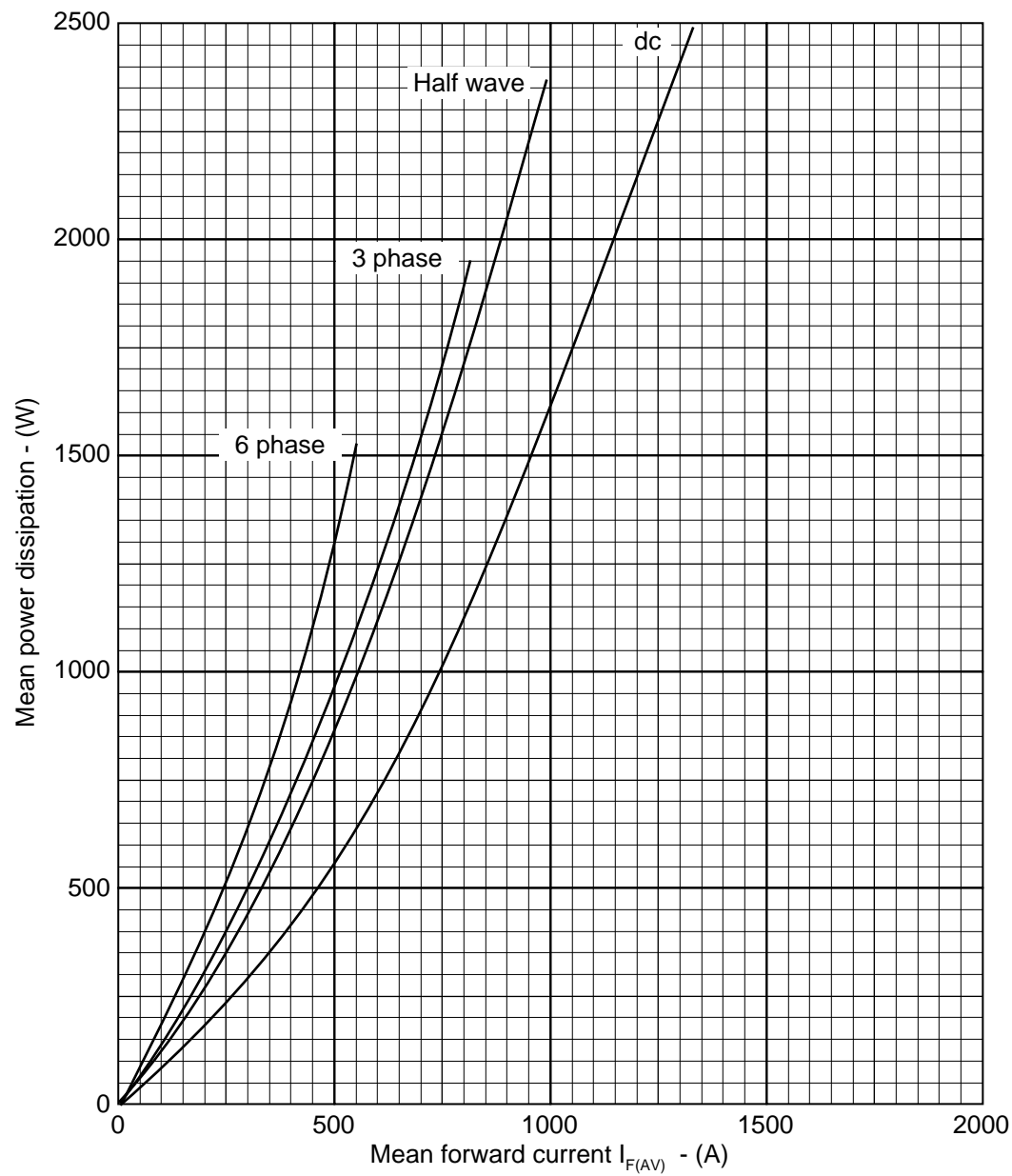
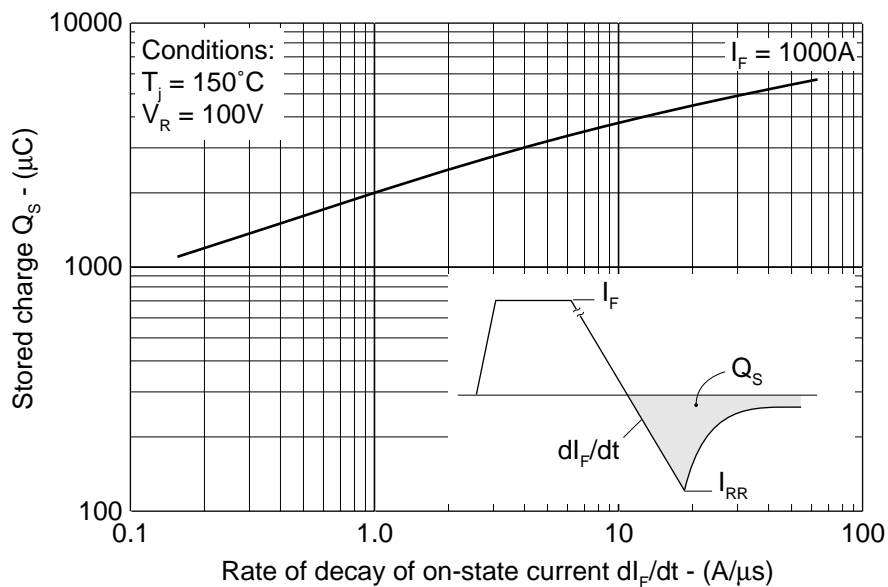
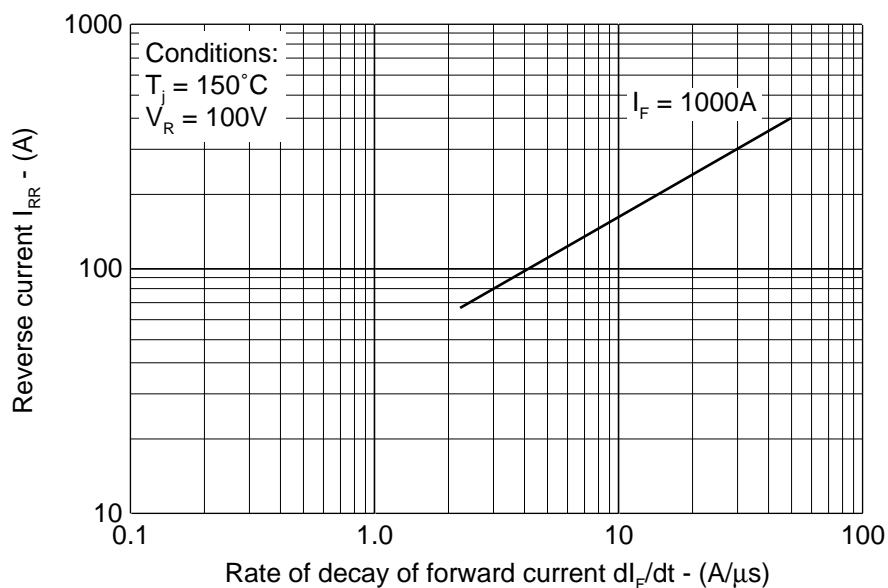


FIG. 2 DISSIPATION CURVES

**FIG. 3 MAXIMUM TOTAL STORED CHARGE****FIG. 4 MAXIMUM REVERSE RECOVERY CURRENT**

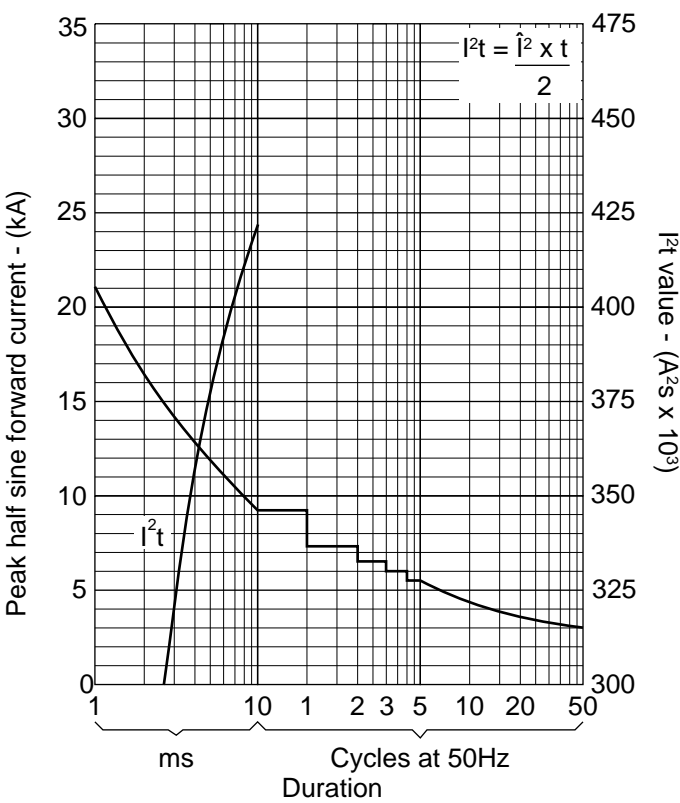


FIG. 5 SURGE (NON-REPETITIVE) FORWARD CURRENT vs TIME (WITH 50% V_{RRM} $T_{case} = 150^{\circ}C$)

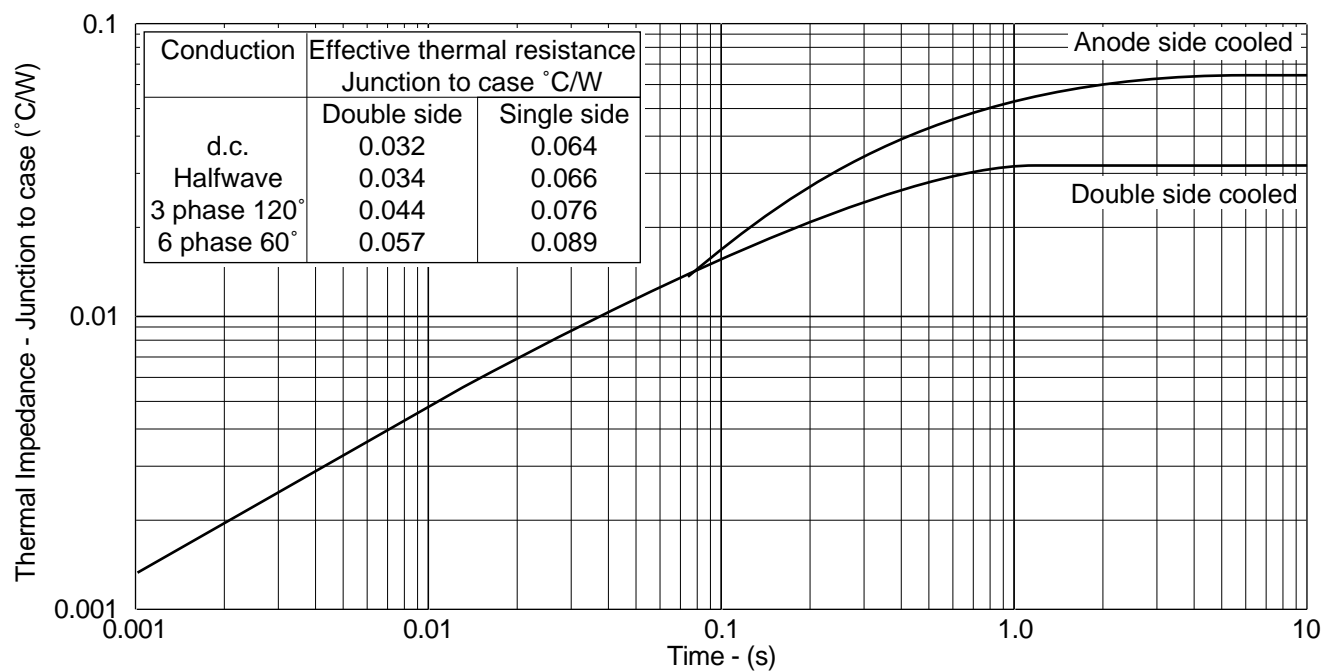
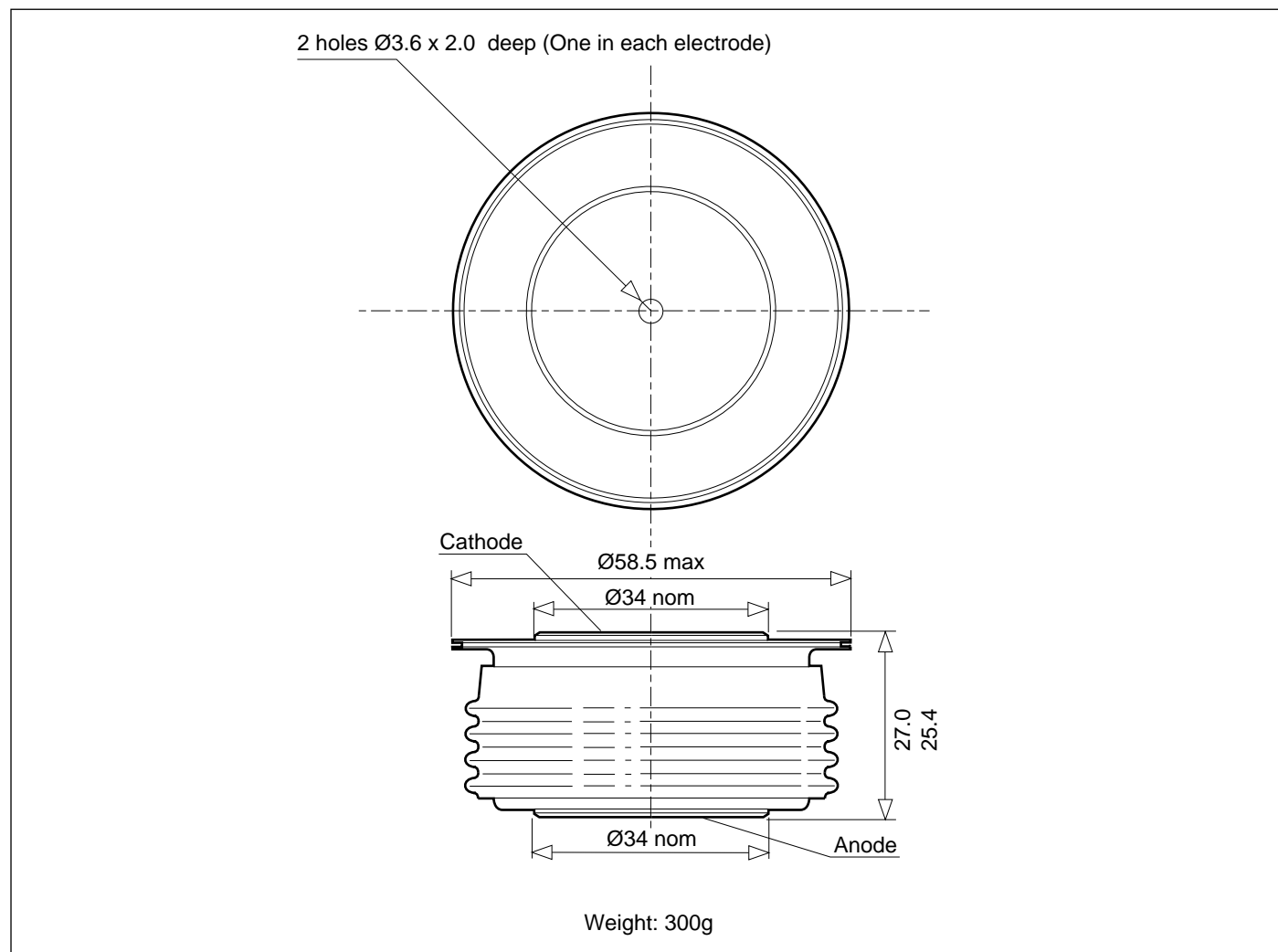


FIG. 6 TRANSIENT THERMAL IMPEDANCE - JUNCTION TO CASE - ($^{\circ}C/W$)

PACKAGE DETAILS - G

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





HEADQUARTERS OPERATIONS

GEC PLESSEY SEMICONDUCTORS

Cheney Manor, Swindon,
Wiltshire, SN2 2QW, United Kingdom.

Tel: + 44 (0)1793 518000

Fax: + 44 (0)1793 518411

GEC PLESSEY SEMICONDUCTORS

P.O. Box 660017

1500 Green Hills Road,
Scotts Valley, California 95067-0017,
United States of America.

Tel: + 1 (408) 438 2900

Fax: + 1 (408) 438 5576

POWER PRODUCT CUSTOMER SERVICE CENTRES

- **FRANCE.** 2 rue Henri-Bergson, 92665 Asnieres Cedex.
Tel: + 33 1 40 80 54 00. Fax: + 33 1 40 80 55 87.
- **GERMANY.** Ungererstrasse 129, 80505 München.
Tel: + 49 (0)89 36 09 060. Fax: + 49 (0)89 36 09 06 55.
- **NORTH AMERICA.** Two Dedham Place, Suite 125, 3 Allied Drive, Dedham. MA 02026.
Tel: + 1 617 251 0126. Fax: + 1 617 251 0106.
- **UNITED KINGDOM.** Doddington Road, Lincoln. LN6 3LF.
Tel: + 44 (0)1522 500500. Fax: + 44 (0)1522 500550.

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